

General Description

The HSBA4072C is the high cell density SGT N-ch MOSFETs, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The HSBA4072C meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

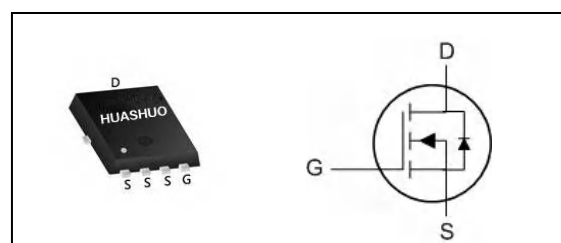
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density SGT MOS Technology

Product Summary

V_{DS}	40	V
$R_{DS(ON),typ}$	1.5	m Ω
I_D	130	A

PRPAK5x6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	130	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	82	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	27	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	22	A
$I_D@T_A=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	17	A
I_{DM}	Pulsed Drain Current ²	400	A
EAS	Single Pulse Avalanche Energy ³	165	mJ
I_{AS}	Avalanche Current	57	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	50	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.5	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	---	1.5	1.9	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	2.5	3.0	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.1	1.8	2.3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=10V, I_D=20A$	---	48	---	nC
Q_{gs}	Gate-Source Charge		---	7.5	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V, V_{GS}=10V, R_G=3\Omega$ $I_D=20A$	---	10	---	ns
T_r	Rise Time		---	40	---	
$T_{d(off)}$	Turn-Off Delay Time		---	39	---	
T_f	Fall Time		---	24	---	
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$	---	2680	---	pF
C_{oss}	Output Capacitance		---	857	---	
C_{rss}	Reverse Transfer Capacitance		---	80	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
T_{rr}	Reverse Recovery Time	$I_F=20A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	49	---	nS
Q_{rr}	Reverse Recovery Charge		---	50	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=57A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package Limitation current is 100A.

Typical Characteristics

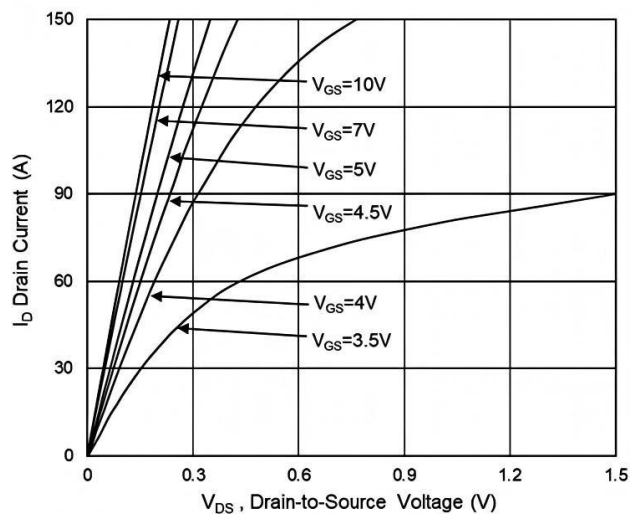


Fig.1 Typical Output Characteristics

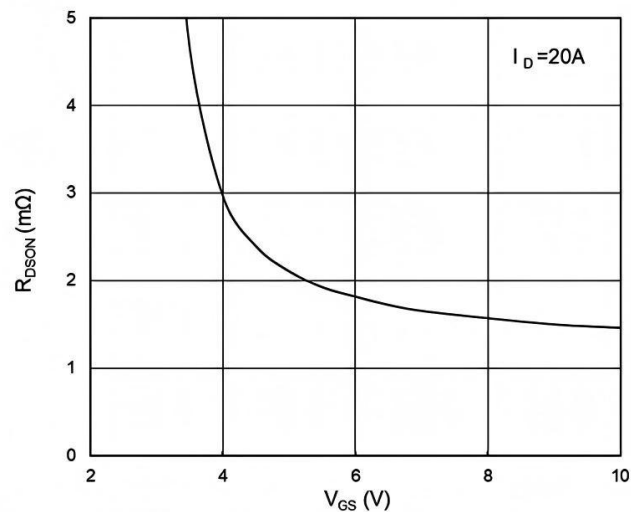


Fig.2 On-Resistance vs. G-S Voltage

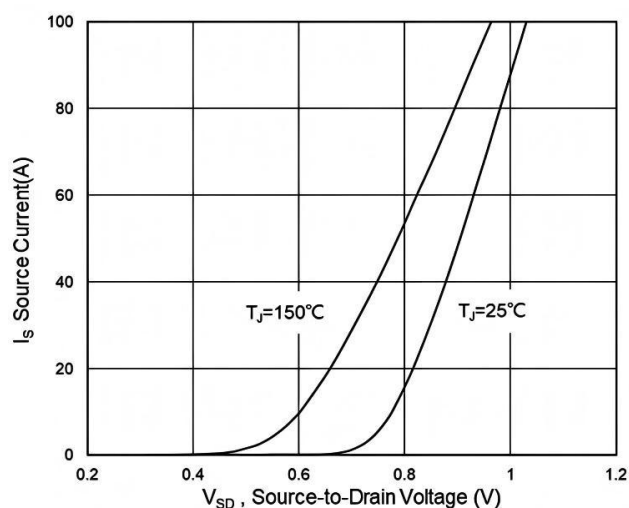


Fig.3 Forward Characteristics of Reverse

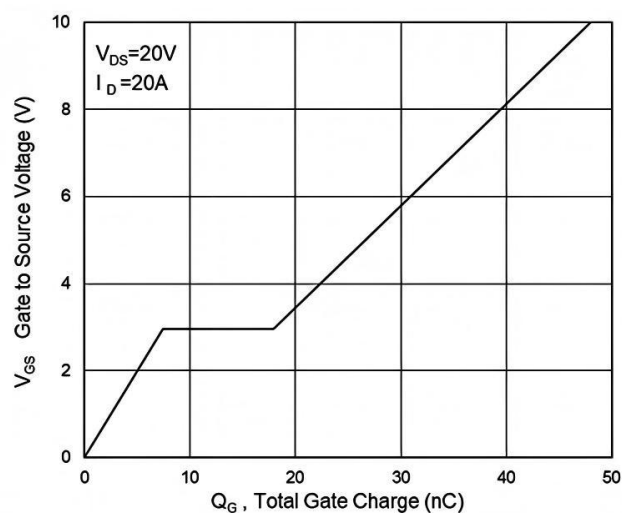


Fig.4 Gate-Charge Characteristics

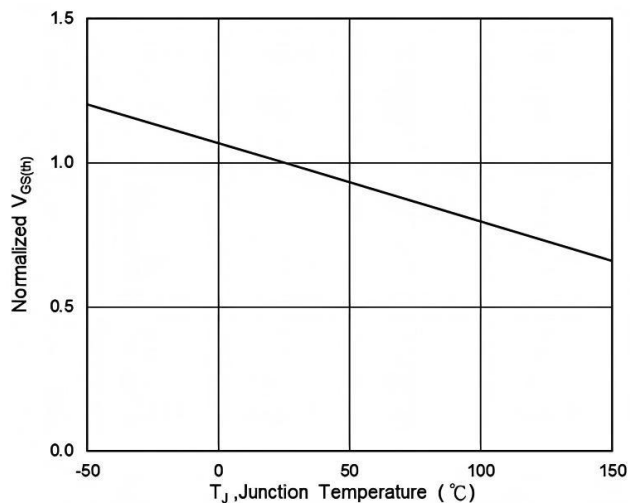


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

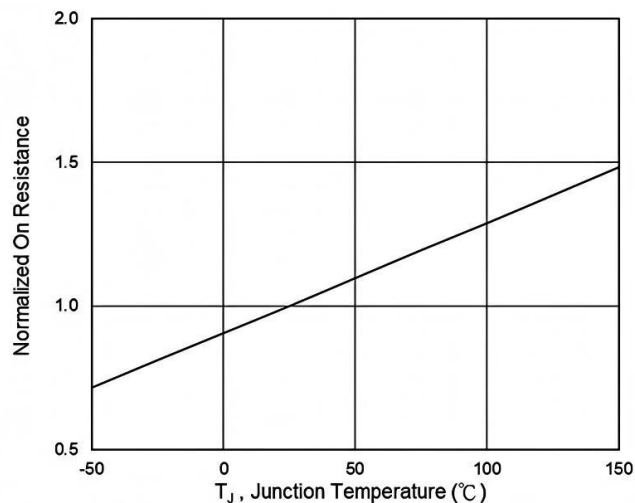


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



N-Ch 40V Fast Switching MOSFETs

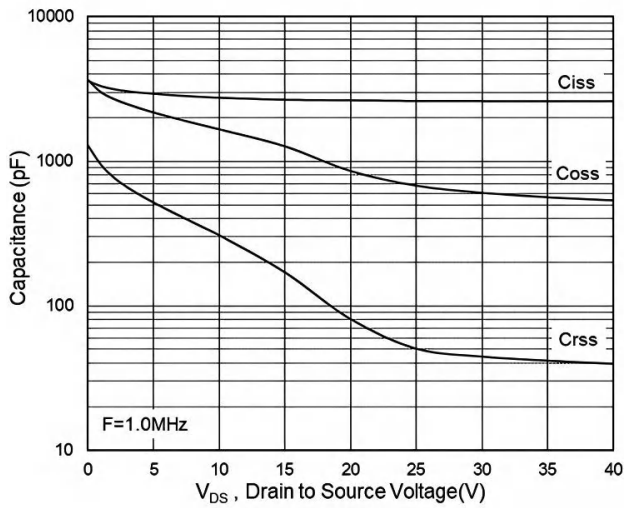


Fig.7 Capacitance

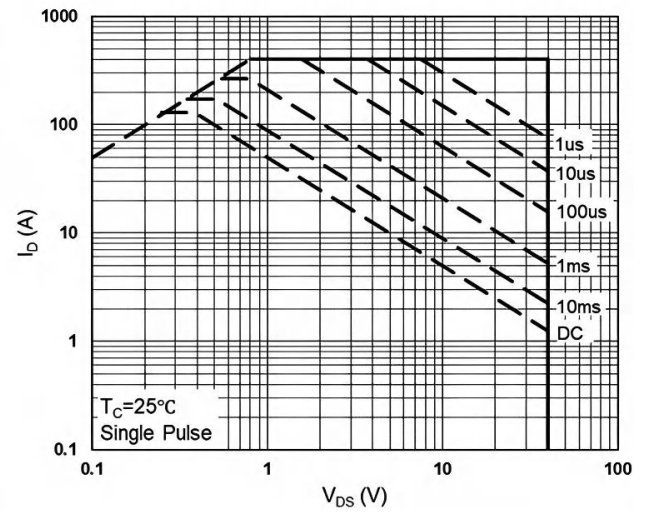


Fig.8 Safe Operating Area

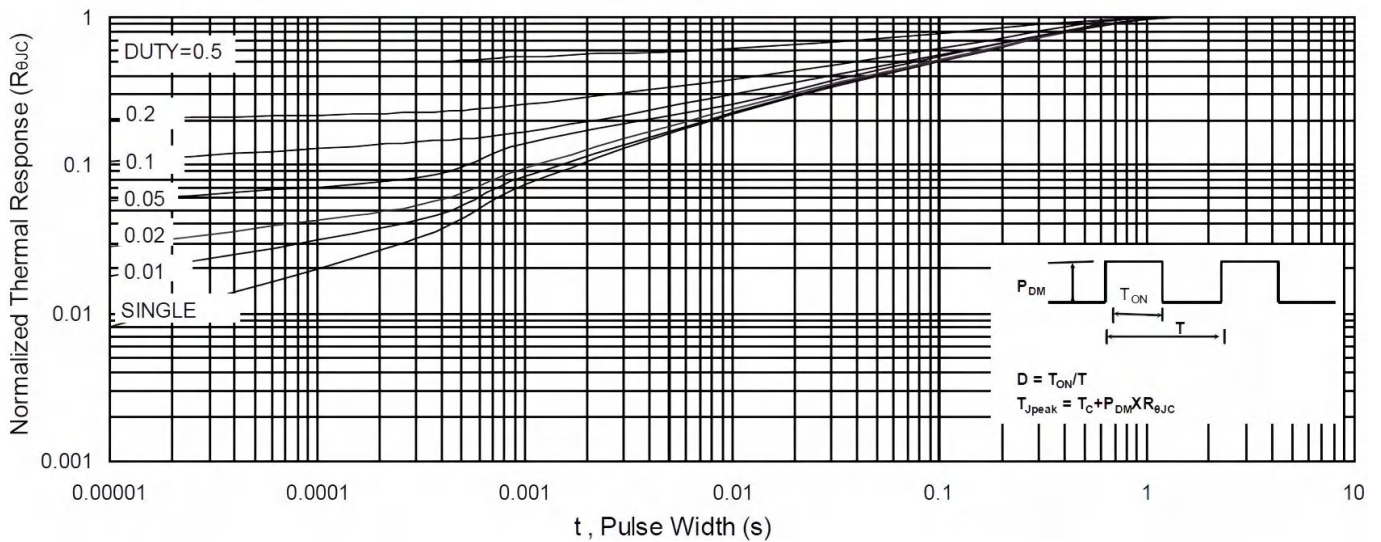


Fig.9 Normalized Maximum Transient Thermal Impedance

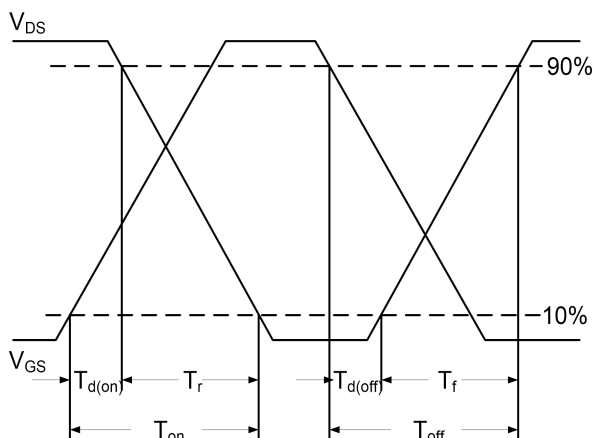


Fig.10 Switching Time Waveform

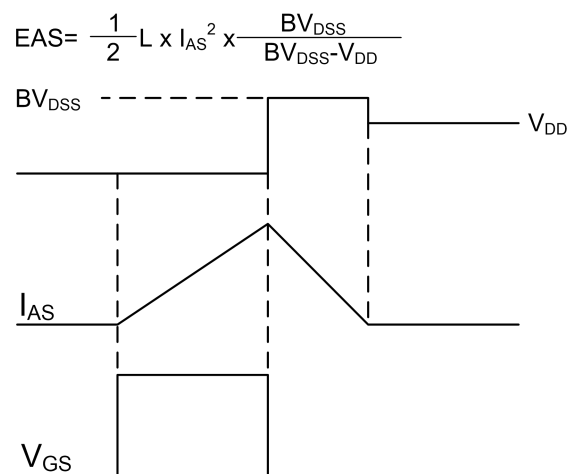
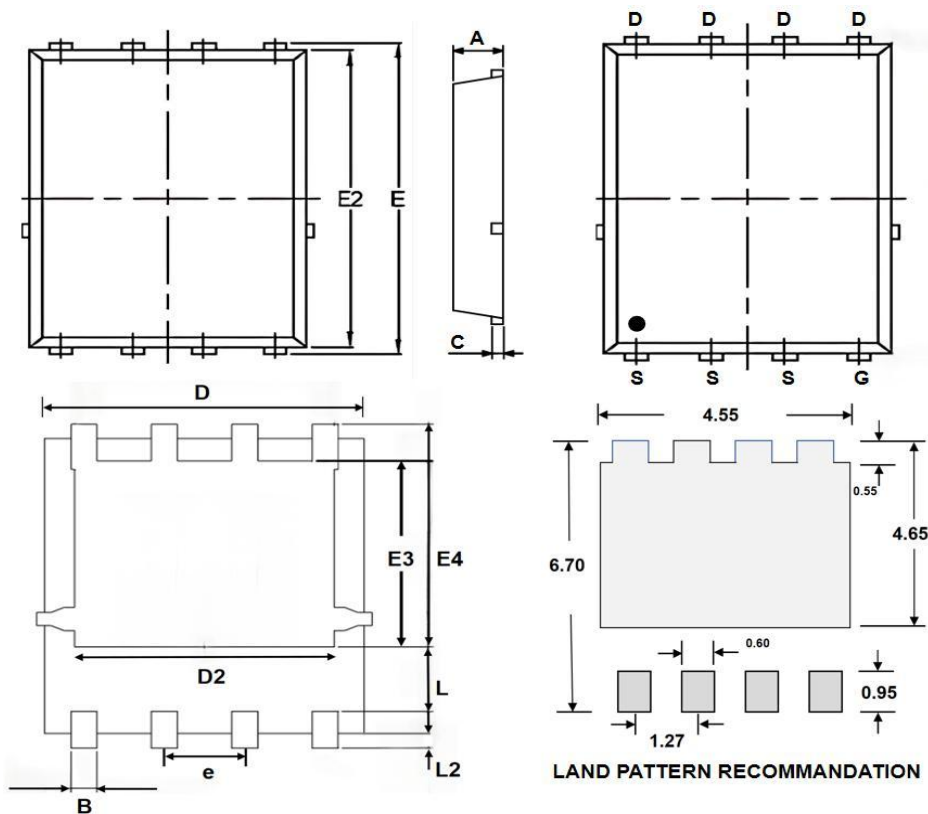


Fig.11 Unclamped Inductive Switching Wave

Ordering Information

Part Number	Package code	Packaging
HSBA4072C	PRPAK5*6	3000/Tape&Reel

PRPAK5*6 Package Outline



LAND PATTERN RECOMMENDATION

SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.25	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.45	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	6.06	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

HSBA4072C Marking:

